N-Channel 30-V(D-S) MOSFET

GENERAL DESCRIPTION

The ME4856 is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching , and low in-line power loss are needed in a very small outline surface mount package.

FEATURES

- $R_{DS(ON)} \leqq 6m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} \leqq 8.5m\Omega @ V_{GS}=4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

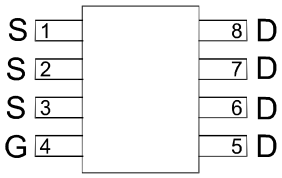
APPLICATIONS

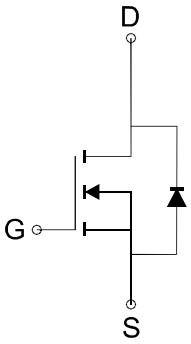
- Power Management in Note book
- Battery Powered System
- DC/DC Converter
- Load Switch

PIN CONFIGURATION

(SOP-8)

Top View





N-Channel MOSFET

Ordering Information: ME4856 (Pb-free)

ME4856-G (Green product-Halogen free)

Absolute Maximum Ratings (T_A=25℃ Unless Otherwise Noted)

Parameter		Symbol	Maximum Ratings	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25℃	I_D	16	A
	T_A=70℃		12.9	
Pulsed Drain Current		I_{DM}	65	A
Maximum Power Dissipation	T_A=25℃	P_D	2.5	W
	T_A=70℃		1.6	
Operating Junction and Storage Temperature Range		TJ, Tstg	-55 to 150	℃
Thermal Resistance-Junction to Ambient*		$R_{\theta JA}$	50	℃/W

* The device mounted on 1in^2 FR4 board with 2 oz copper

N-Channel 30-V(D-S) MOSFET

Electrical Characteristics (T_A=25℃ Unless Otherwise Specified)

Symbol	Parameter	Limit	Min	Typ	Max	Unit
STATIC						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	30			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.3	1.8	3	V
I_{GSS}	Gate Leakage Current	V_{DS}=0V, V_{GS}=±20V			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V			1	μA
$R_{DS(ON)}$	Drain-Source On-State Resistance [a]	V_{GS}=10V, I_D= 10A		4.5	6	mΩ
		V_{GS}=4.5V, I_D= 7.5A		6.5	8.5	
V_{SD}	Diode Forward Voltage	I_S=2.7A, V_{GS}=0V		0.72	1.1	V
DYNAMIC						
Qg	Total Gate Charge(10V)	V_{DS}=15V, V_{GS}=10V, I_D=17A		55		nC
Qg	Total Gate Charge(4.5V)	V_{DS}=15V, V_{GS}=4.5V, I_D=17A		29		
Qgs	Gate-Source Charge			10		
Qgd	Gate-Drain Charge			15		
Ciss	Input capacitance	V_{DS}=15V, V_{GS}=0V, f=1.0MHz		2400		pF
Coss	Output Capacitance			350		
Crss	Reverse Transfer Capacitance			110		
Rg	Gate-Resistance	V_{DS}=0V, V_{GS}=0V, f=1MHz		1.2		Ω
$t_{d(on)}$	Turn-On Delay Time	V_{DD}=15V, R_L =15Ω I_D=1A, V_{GEN}=10V R_G=6Ω		23		ns
t_r	Turn-On Rise Time			12		
$t_{d(off)}$	Turn-Off Delay Time			86		
t_f	Turn-Off Fall Time			12		

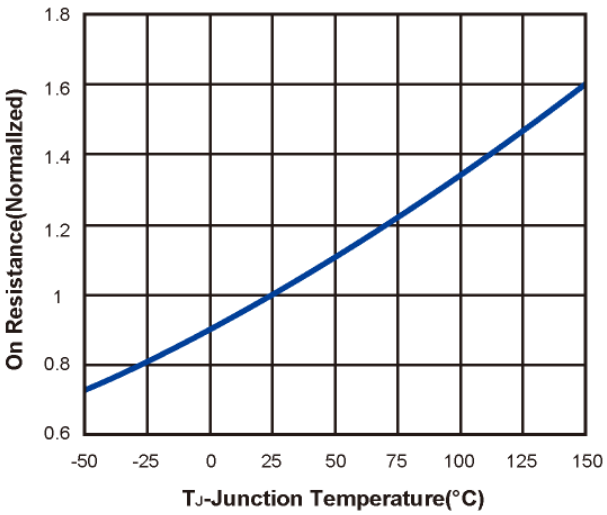
Note: a: Pulse test: pulse width＜=300us, duty cycle＜=2%

b. Matsuki Electric/ Force mos reserves the right to improve product design, functions and reliability without notice.

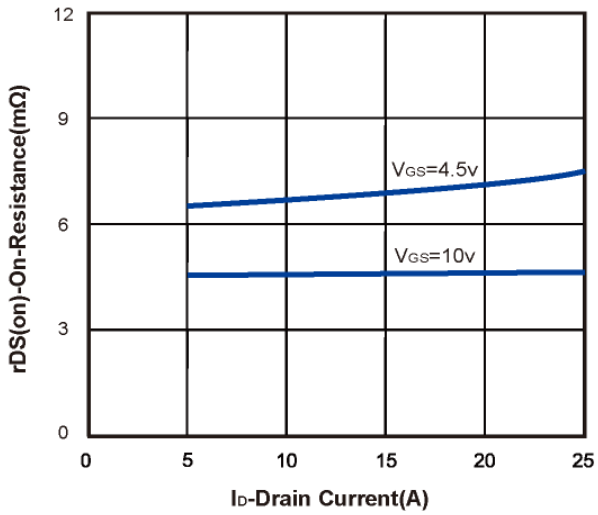
N-Channel 30-V(D-S) MOSFET

Typical Characteristics (T_J =25℃ Noted)

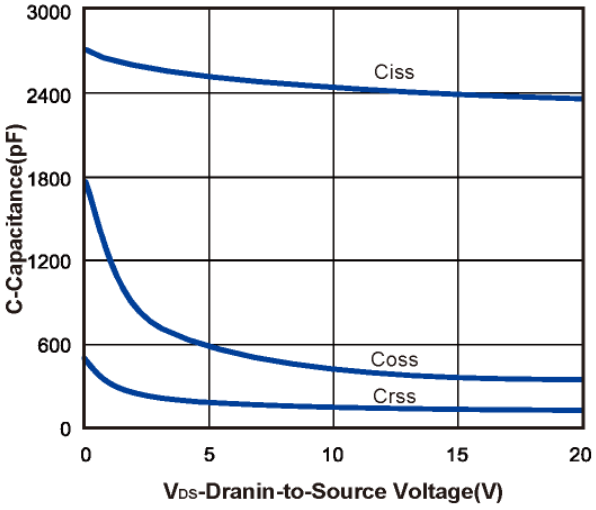
On Resistance vs. Junction Temperature



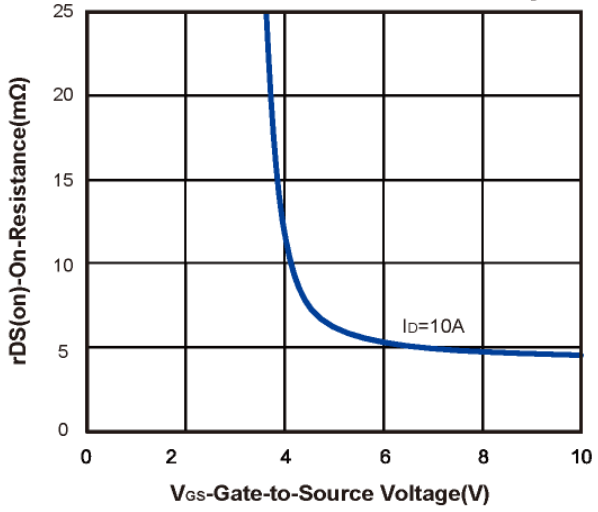
On Resistance vs. Drain Current



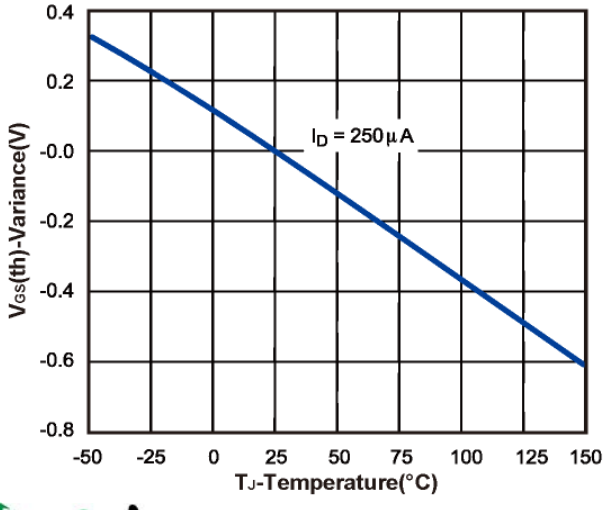
Capacitance



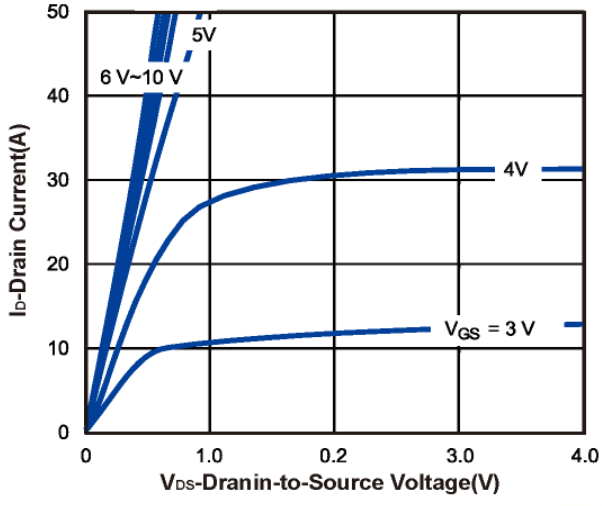
On Resistance vs. Gate-to-Source Voltage



Threshold Voltage



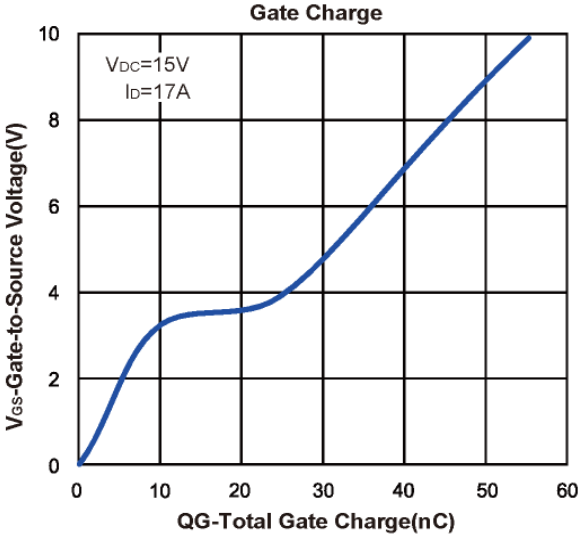
On-Region Characteristics



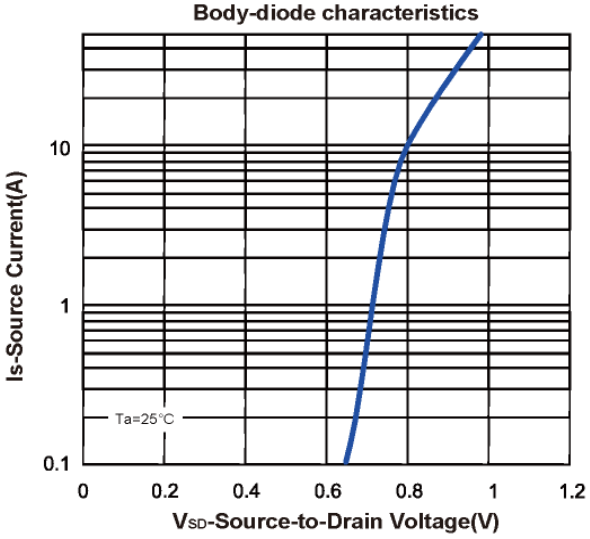
N-Channel 30-V(D-S) MOSFET

Typical Characteristics (T_J =25℃ Noted)

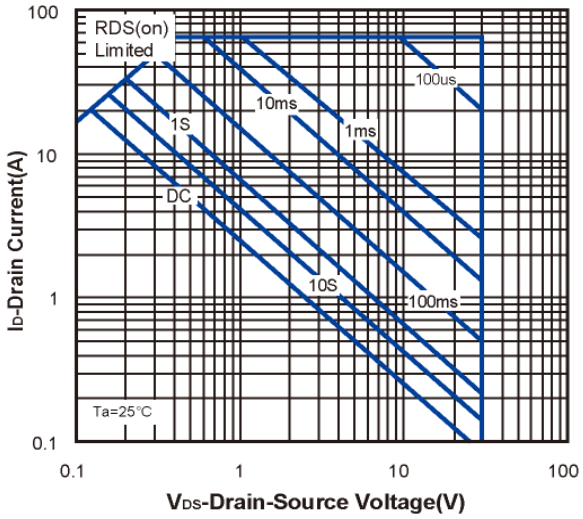
Gate Charge



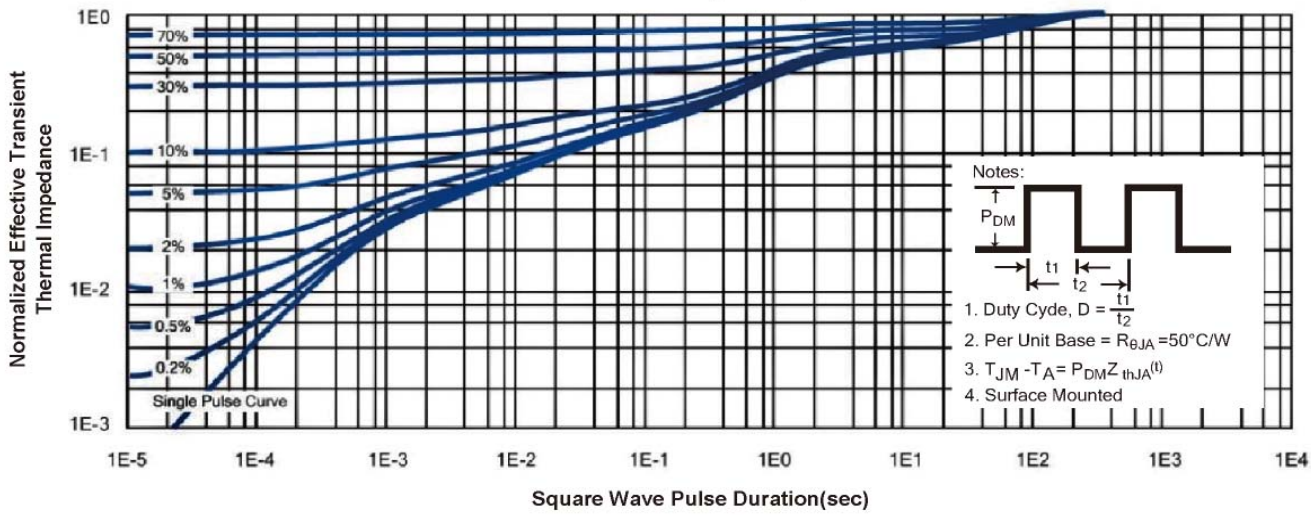
Body-diode characteristics



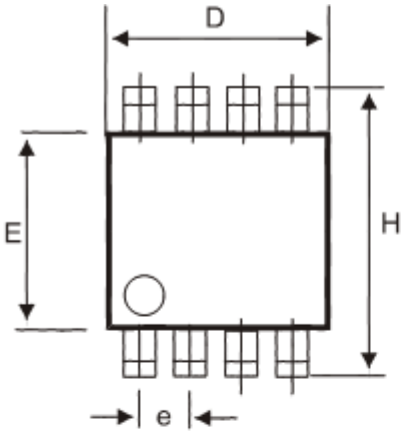
Maximum Forward Biased Safe Operating Area

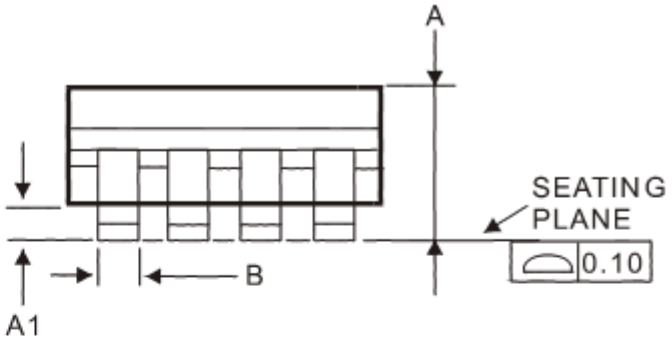


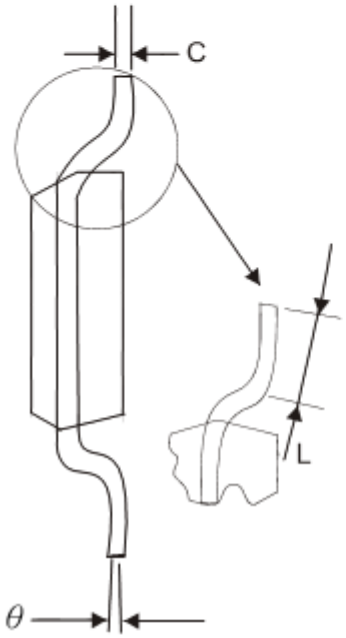
Normalized Thermal Transient Impedance, Junction-to-Ambient



SOP-8 Package Outline







DIM	MILLIMETERS (mm)	
	MIN	MAX
A	1.35	1.75
A1	0.10	0.25
B	0.35	0.49
C	0.18	0.25
D	4.80	5.00
E	3.80	4.00
e	1.27 BSC	
H	5.80	6.20
L	0.40	1.25
θ	0°	7°

Note: 1. Refer to JEDEC MS-012AA.

2. Dimension “D” does not include mold flash, protrusions or gate burrs . Mold flash, protrusions or gate burrs shall not exceed 0.15 mm per side.